

none

none

none

© EPODOC / EPO

PN - JP5129226 A 19930525

PD - 1993-05-25

PR - JP19910287773 19911101

OPD - 1991-11-01

TI - MANUFACTURE OF SEMICONDUCTOR DEVICE

IN - EGUCHI YOSHIKAZU

PA - SEIKO EPSON CORP

IC - H01L21/28 ; H01L21/285 ; H01L21/3205 ; H01L21/90

© WPI / DERWENT

TI - Forming wiring for semiconductor device - includes oxidising refractory metal silicide on semiconductor substrate before forming interlayer insulating film, tungsten@ filled contact hole, and aluminium@ wiring NoAbstract

PR - JP19910287773 19911101

PN - JP5129226 A 19930525 DW199325 H01L21/28 004pp

PA - (SHIH ) SEIKO EPSON CORP

IC - H01L21/28 ;H01L21/285 ;H01L21/3205

OPD - 1991-11-01

AN - 1993-201902 [25]

© PAJ / JPO

PN - JP5129226 A 19930525

PD - 1993-05-25

AP - JP19910287773 19911101

IN - EGUCHI YOSHIKAZU

PA - SEIKO EPSON CORP

TI - MANUFACTURE OF SEMICONDUCTOR DEVICE

AB - PURPOSE:To realize good burying inside a contact hole by a metal by forming a good barrier metal in a wiring formation process of a semiconductor device.

- CONSTITUTION:A high melting point metal silicide103 is formed on a semiconductor substrate 101 and an oxide layer 104 which becomes a barrier metal is further formed by exposing it to oxygen plasma. Thereafter, layer insulating film 108 and a contact hole 105 are formed and a tungsten film 107 is deposited by sputtering method as an adherent layer, and a tungsten film 108 is deposited through chemical vapor reaction method. After tungsten in a region inside and outside of the contact hole is removed, an aluminum

none

none

none

none

none

none

copper/alloy film 109 is deposited and a wiring is completed by patterning.

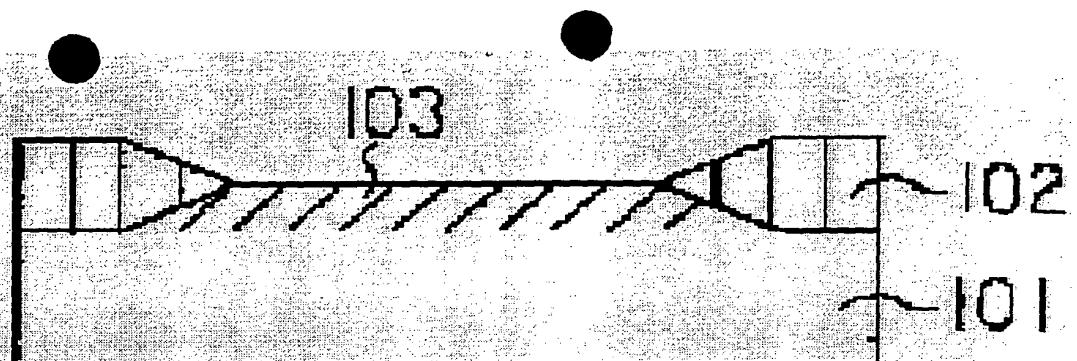
- H01L21/28 ;H01L21/285 ;H01L21/3205 ;H01L21/90

none

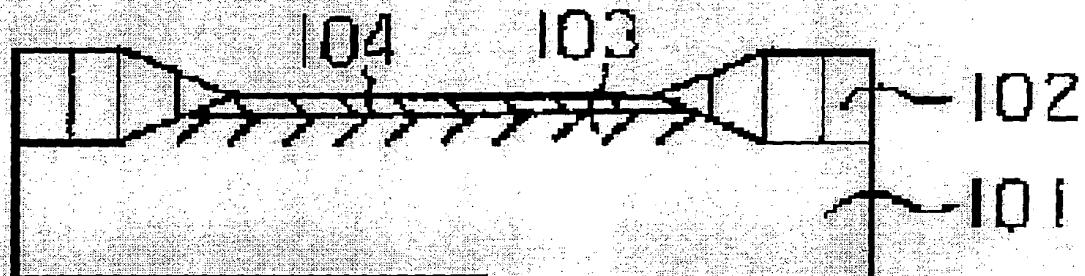
none

none

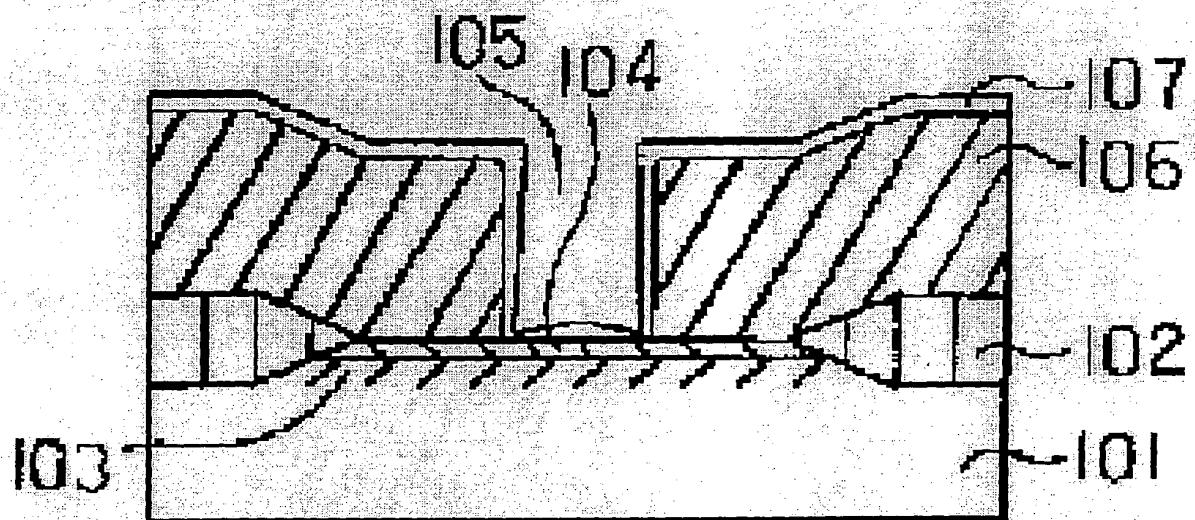
(a)



(b)



(c)



(d)

